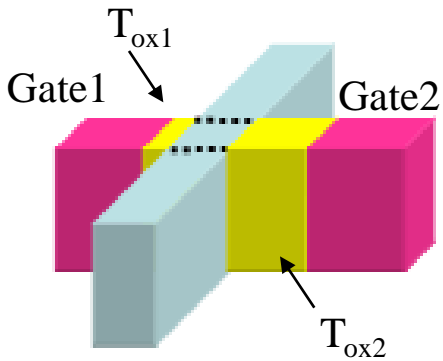
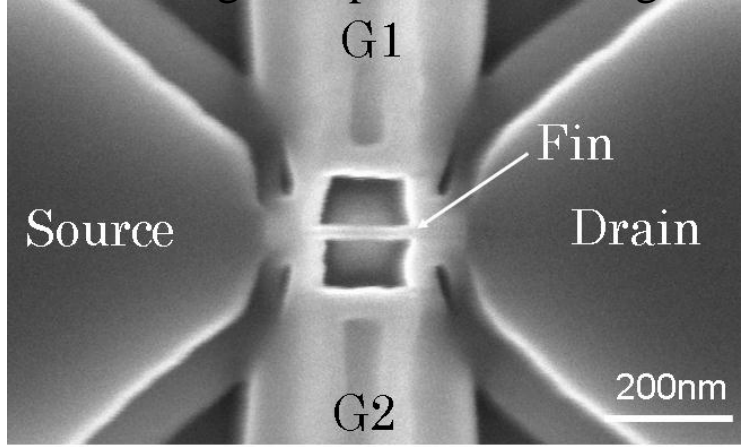


Four-terminal FinFET Fabrication using NBO (300°C) Process

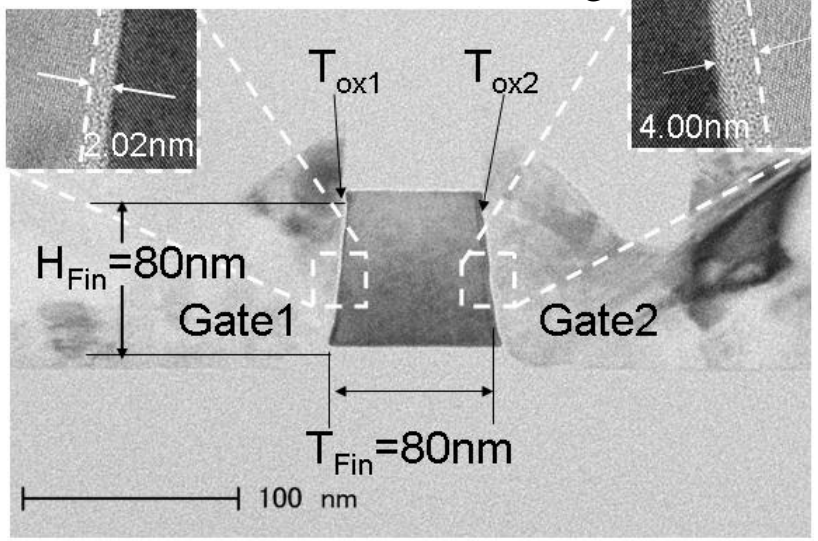
Asymmetric T_{ox} four-terminal FinFET



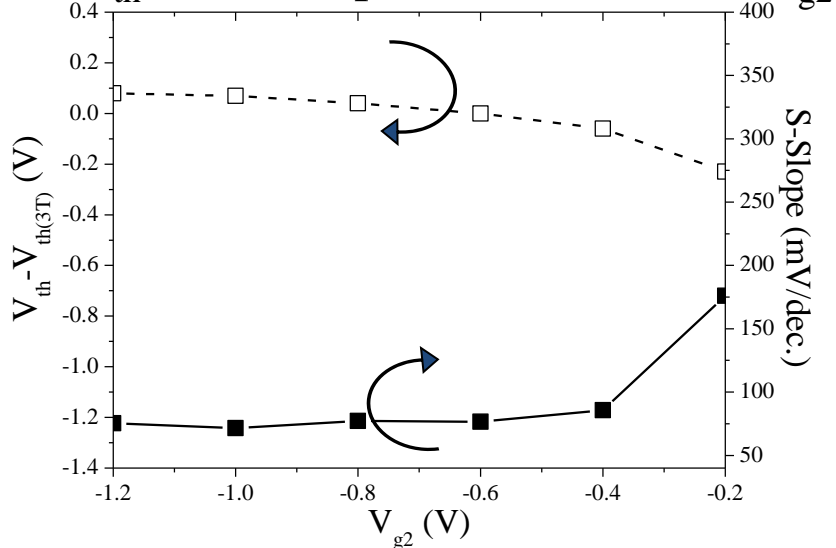
SEM image of 4T-FinFET after gate separation etching



Cross-sectional TEM image



The V_{th} and S-slope as a function of V_{g2}



We successfully fabricated asymmetric T_{ox} four-terminal FinFET using NBO process.